

Case Docket No. TOPTICS.018A

Date: September 1, 2004

IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

Applicant(s)

Gene H. Haertling

Appl. No.

09/891,689

Filed

June 26, 2001

For

DEACTIVATED ELECTRO-

OPTIC MATERIAL AND METHOD OF FORMING THE

SAME

Examiner

Evelyn A. Lester

Group Art Unit:

2873

I hereby certify that this correspondence and all marked attachments are being deposited with the United States Postal Service as first class mail in an envelope addressed to: Commissioner for Patents, P.O. Box 1450, Alexandria, VA 22313-1450, on

September 1, 2004

TRANSMITTAL LETTER

Commissioner for Patents P.O. Box 1450 Alexandria, VA 22313-1450

Dear Sir:

Enclosed for filing in the above-identified application are:

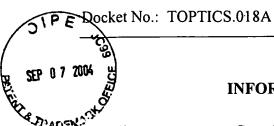
- An Information Disclosure Statement. (X)
- A PTO Form 1449 with twenty-five (28) references. (X)
- The Commissioner is hereby authorized to charge any additional fees which may be required, or (X) credit any overpayment, to Account No. 11-1410.
- Return prepaid postcard. (X)

Mark J. Gallaghen

Registration No. 43,622

Attorney of Record Customer No. 20,995

(949) 760-0404



INFORMATION DISCLOSURE STATEMENT

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Evelyn A. Lester

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Commissioner for Patents P.O. Box 1450 Alexandria, VA 22313-1450

Dear Sir:

Enclosed is form PTO-1449 listing 28 references that are also enclosed.

This Information Disclosure Statement is being filed before the receipt of a first Office Action on the merits after the filing of a Request for Continued Examination and presumably no fee is required in accordance with 37 C.F.R. § 1.97(b)(4). If a first Office Action on the merits was mailed before the mailing date of this Statement, the Commissioner is authorized to charge the fee set forth in 37 C.F.R. § 1.17(p) to Deposit Account No. 11-1410.

Respectfully submitted,

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U.S. DEPARTMENT OF COMMERCE PATENT AND TRADEMARK OFFICE

ATTY. DOCKET NO. TOPTICS.018A APPLICATION NO. 09/891,689

INSPRMATION DISCLOSURE STATEMENT
BY APPLICANT

E SEVERAL SHEETS IF NECESSARY)

APPLICANT Gene H. Haertling

FILING DATE June 26, 2001 GROUP 2873

	U.S. PATENT DOCUMENTS						
EXAMINER INITIAL		DOCUMENT NUMBER	DATE	NAME	CLASS	SUBCLASS	FILING DATE (IF APPROPRIATE)
	1.	4,201,442	05/1980	McMahon et al.			
	2.	4,796,982	01/1989	Kitabatake et al.			
	3.	4,993,811	02/19/91	Blazey et al.			
	4.	5,011,271	04/30/91	Saito et al.			
	5.	5,016,959	05/1991	Diemeer			
-	6.	5,745,280	4/1998	Kitano			
	7.	5,369,718	11/1994	Kamata et al.			
	8.	5,911,018	6/1999	Bischel et al.			

				FOREIGN PATENT DOCUMENTS				
EXAMINER		DOCUMENT NUMBER	DATE	COUNTRY	CLASS	SUBCLASS	TRANS	LATION
INITIAL							YES	NO
	9.	0 344 857 A1	05/1989	Europe				

EXAMINER INITIAL	OTHER DOCUMENTS (INCLUDING AUTHOR, TITLE, DATE, PERTINENT PAGES, ETC.)						
	10.	Antiferroelectric-Phase PLZT For Use In High Density Optical Data Storage, S. Mancha, J. Bullington, R. Carter and C. Dehainaut, Airforce Weapons Laboratory (AFSC) Kirtland Airforce Base New Mexico, Ferroelectrics, 1988 Gordon and Breach Science Publishers S.A., Vol. 82, pp. 99-104.					
	11.	Crystallization of Lanthanum-Modified Lead Zirconate Titanate (PLZT) Using Coprecipitated Gels, Yao-Jung Lee, Fu-Su Yen, Jong-Ping Wu and Hsing-I Hsiang, Jpn. J. Appl. Phys., Vol. 34, Pt. 1, No. 8A, August 1995, pp. 4137-4142.					
	12.	Crystallization of Silicon on Electro-Optic PLZT by a Laser Beam Modulated in Shape and Intensity Profile, T.H. Lin, M.L. Burgener, S.C. Esener and S.H. Lee, Mat. Res. Soc. Symp. Proc., Vol. 74, 1987, pp. 135-140.					
	13.	Dielectric Properties of (111) and (100) Lead-Zirconate-Titanate Films Prepared by Sol-Gel Technique, K. Aoki et al., Jpn. J. Appl. Phys., Vol. 33 (1994) Pt. 1, No. 9B, pp. 5155-5158.					
	14.	Effects of O3 on Growth and Electrical Properties of Pb(Zr, Ti)O3 Thin Films by Photoenhanced Metalorganic Chemical Vapor Deposition, Masaru Shimizu et al., Jpn. J. Appl. Phys., Vol. 33 (1994) Pt. 1, No. 9B, pp. 5135-5138.					
	15.	Electric and Optical Properties of PLZT Ceramic Shutter Array, Y. Takubo et al., Jpn. J. Appl. Phys., Vol. 24 (1985) Supplement 24-3, pp. 159-161.					
	16.	Fabrication of Transparent PLZT Ceramics by Atomsphere Sintering, Katsuhiko Tanaka et al., Japanese Journal of Applied Physics Vol. 24 (1985) Supplement 26-3, pp. 107-109.					
	17.	Fabrication of Transparent PLZT Ceramics with a High Transmittance and Their Application to Optical Light Shutter, Kunihiko Hayashi, et al., Proceedings of the 6 th Meeting on Ferroelectric Materials and Their Applications, Kyoto 1987, Japanese Journal of Applied Physics, Vol. 26 (1987) Supplement 26-2, pp. 126-128.					
	18.	High Speed Optical TIR Switches Using PLZT Thin-Film Waveguides on Sapphire, Hidetaka Higashino, Takao Kawaguchi, Hideaki Adachi, Toshihiko Makino and Osamu Yamazaki, Proceedings of the Sixth International meeting on Ferroelectricity, Kobe, 1985, Jpn. J. Appl. Phys. Vol 24 (1985) Suppl. 24-2, p. 284-286.					

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*EXAMINER: INITIAL IF CITATION CONSIDERED, WHETHER OR NOT CITATION IS IN CONFORMANCE WITH MPEP 609; DRAW LINE THROUGH CITATION IF NOT IN CONFORMANCE AND NOT CONSIDERED, INCLUDE COPY OF THIS FORM WITH NEXT COMMUNICATION TO APPLICANT.

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APPLICATION NO. 09/891,689

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FILING DATE June 26, 2001 **GROUP** 2873

EXAMINER INITIAL	OTHER DOCUMENTS (INCLUDING AUTHOR, TITLE, DATE, PERTINENT PAGES, ETC.)						
	19.	Optical Switch Utilizing Total Reflection of (Pb, La) (Zr, Ti)O ₃ Ceramics, Toshio Utsunomiya, Jpn J. Appl. Phys. Vol. 33 (1994) pp. 5440-5442 Part 1, No. 9B, September 1994.					
	20.	Optical TIR Switches Using PLZT Thin-Film Waveguides on Sapphire, Kiyotaka Wasa et al., <u>Journal of Lightwave Technology</u> , Vol. LT-2, No. 5, pp. 710-713, October 1984.					
	21.	A (Pb, La)(Zr, Ti)O3 (PLZT) Polarization-Plane with a Buried Electrode Structure for a Mid-Infrared Electro-Optical Shutter, Yoshiharu Taniguchi, Kensuke Murakami, Hiroshi Kobayashi and Shosaku Tanaka, Jpn. J. Appl. Phys., Vol. 36 (1997) Pt. 1, No. 5A, pp. 2709-2714.					
	22.	PLZT Electrooptic Shutter, K. Tanaka et al., Jpn. J. Appl. Phys., Vol. 22 (1983) Supplement 22-2, pp. 126-128.					
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	24.	Preparation and Characterization of Sol-Gel Derived Epitaxial and Oriented Pb(Zr _{0.52} Ti _{0.48})O ₃ Thin Films, Keiichi Nashimoto and Shigetoshi Nakamura, Jpn. J. Appl. Phys., Vol. 33 (1994) Pt. 1, No. 9B, pp. 5147-5150.					
	25.	Preparation of Pb(Zr,Ti)O₃ Thin Films by Sol-Gel Technique, Tomoyasu Takusagawa, Noriaki Yamada, Terumasa Kato, Hajime Hattori and Teruyuki Matsui, Jpn. J. Appl. Phys. Vol. 33, Pt. 1, No. 9B, 1994, pp. 5151-5154.					
	26.	Prism-Type Optical Deflector Using PLZT Ceramics, Toshio Utsunomiya et al., <u>Japanese Journal of Applied Physics</u> , Vol. 24, (1985) Supplement 24-3, pp. 169-171.					
	27.	Uniform Ultra-Thin Pb(Zr, Ti)O3 Films Formed by Metal-Organic Chemical Vapor Deposition and Their Electrical Characteristics, Hiroshi Miki and Yuzuru Ohji, Jpn. J. Appl. Phys., Vol. 33 (1994) Pt. 1, No. 9B, pp. 5143-5146.					
	28.	(Co-pending) U.S. Patent Application No. 10/013,336 (Attorney Docket No. TOPTICS.004CP2)					

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DATE CONSIDERED